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Hierarchical Tin Oxide Octahedra for Highly Efficient Dye-Sensitized Solar Cells

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Since the great breakthrough made in 1991 by O'Regan^[1] and Grätzel^[2], dye-sensitized solar cells (DSSCs) have attracted tremendous interest and are becoming one of the most promising candidates for practical photovoltaic applications due to their low production cost and efficient photovoltaic performance. Up to now, more than 11% power conversion efficiency has been reported for DSSCs based on TiO₂ nanocrystalline photoelectrodes.^[3] It is well known that the composition and structure of the photoelectrode material play an important role in the photovoltaic performance and stability of DSSCs. As an efficient photoelectrode, the material should have a large surface area to adsorb larger amounts of dye and highly ordered nanoarrays or densely packed microstructure for fast electron transport and light scattering.^[4-6] Among the photoelectrodes, one interesting structure is the double-layer electrode containing a dye adsorption layer (10–15 μ m thick, consisting of \approx 20 nm particles) and a light-scattering layer (3-5 µm thick, consisting of a few hundreds of nanometer particles); this has been found to improve the photovoltaic performance.^[7] Another novel photoelectrode is the hierarchically structured film consisting of submicron spheres that are made up of 10-20 nm particles. The photoelectrode consists of this kind of bifunctional material with both the dye adsorption layer (nanoparticles) and the light-scattering layer (submicron spheres), which results in a significant enhancement of power conversion efficiency.^[5,6] However, most of the works have been only focused on the hierarchical TiO₂ or ZnO spheres.^[5,6] Tin oxide, as an n-type semiconductor with a wide direct

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band gap of 3.6 eV at 300 K,^[8] is one of the promising multifunctional materials in gas sensors,^[9] dye-sensitized solar cells,^[10] lithium ion batteries, and so on.^[11] SnO₂ nanoparticles and hollow SnO₂ microspheres have been reported to exhibit about 5% photovoltaic performance.^[10] However, to the best of our knowledge, hierarchically structured octahedral (nonspherical) SnO₂ materials have not yet been reported for DSSCs applications; this might be an ideal structure because the eight faces at the submicron level can have a light-scattering effect.

Herein, we report, for the first time, a rapid and facile sonochemical process to synthesize uniform octahedral $Sn_6O_4(OH)_4$ intermediates, resulting in hierarchical SnO_2 octahedra approximately 1.0 µm in size, consisting of SnO₂ nanoparticles about 30 nm in diameter by heat treatment of the as-made Sn₆O₄(OH)₄ at 800 °C for 3 h in air. The reaction solution containing SnCl₂·2H₂O (1.128 g), diethanolamine (5.0 mL), diethylene glycol (DEG, 40 mL), and deionized water (10 mL) is subjected to intense ultrasonic irradiation for 10 min; the resulting precipitates were collected by centrifugation at 5000 rpm for 5 min. The present sonochemical method has a few clear advantages over traditional hydrothermal processes, such as it is simple, fast, low energy cost, and does not require surfactants or templates.^[12,13] The hierarchical SnO₂ octahedra consisting of nanoparticles were further used as photoelectrodes for DSSC applications, showing a highly efficient power conversion efficiency of 6.40%.

Figure 1 a shows the typical XRD patterns of samples prepared by a sonochemical reaction for 10 min (curve I) and further heat treatment at 800 °C for 3 h (curve II). As shown in curve I, the well-resolved peaks can be indexed to the tetragonal structure $Sn_6O_4(OH)_4$ (JCPDS card no. 46-1486) with cell constants of a=b=7.927 and c=9.102 Å. After calcination of the as-prepared samples, all intense diffraction peaks (curve II) are in good agreements with rutile-like tetragonal structure of SnO_2 (JCPDS card no. 41-1445) with cell constants of a=b=4.738 and c=3.187 Å. It shows that n-type SnO_2 semiconductor powders are obtained through





Figure 1. a) Powder X-ray diffraction patterns of as-synthesized $Sn_6O_4(OH)_4$ sample after sonochemical reaction for 10 min (curve I) and SnO_2 octahedra with a heat treatment at 800 °C for 3 h (curve II). b) and c) are the FE-SEM images of as-prepared $Sn_6O_4(OH)_4$ octahedra and calcined hierarchical octahedral SnO_2 , respectively. Insets in b) and c) are the high-magnification FE-SEM images of $Sn_6O_4(OH)_4$ and SnO_2 , respectively. Insets in b) and c) are the high-magnification FE-SEM images of $Sn_6O_4(OH)_4$ and SnO_2 , respectively. d) TEM image of SnO_2 octahedra. Upper and lower insets are an individual SnO_2 octahedron and the corresponding diffraction pattern, respectively. e) Schematic models of an ideal SnO_2 octahedron projected in different directions: α): [001], β): [110], γ): [$\overline{111}$], δ): [$\overline{110}$], which are related to the SnO_2 octahedron marked in Figure 1d. f) Model of an ideal octahedron.

the oxidization and decomposition of as-prepared $Sn_6O_4(OH)_4$ during calcination.

The morphology of the as-prepared $Sn_6O_4(OH)_4$ and calcined SnO_2 was characterized by field-emission scanning electron microscopic (FE-SEM), shown in Figure 1 b and c, respectively. It is interesting to note that the uniform $Sn_6O_4(OH)_4$ octahedra were easily observed after the simple and fast sonochemical reaction (10 min). The $Sn_6O_4(OH)_4$ octahedron has eight very smooth equilateral triangles faces with an average edge length of 1.0 µm, and the dihedral angle for each set of two conjoined faces were measured to be about (60 ± 1), (56 ± 1),and (64 ± 1)°, respectively, which

are close to the theoretic value (60°) of an octahedron. After heat treatment of the as-prepared octahedral Sn₆O₄(OH)₄ at 800 °C for 3 h, the hierarchical SnO₂ octahedra consisting of nanoparticles were observed, shown in Figure 1 c. The octahedral morphology of SnO2 remains constant even after calcination. The rough surface clearly reveals the hierarchical SnO₂ octahedra are composed of nanoparticles approximately 30 nm in diameter (inset in Figure 1 c).

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The octahedral SnO₂ were further characterized by TEM, high-resolution TEM (HRTEM), and selected-area electron diffraction (SAED) analyses, as shown in Figure 1d and Figure S1 in the Supporting Information. The low-magnification TEM image (Figure 1d) clearly reveals the octahedral structure of SnO₂ sample. Sev-SnO₂ octahedra eral are marked by $\alpha,\,\beta,\,\gamma,$ and $\delta,$ which are viewed along [001], [110], $[\bar{1}\bar{1}1]$, and $[\bar{1}10]$ directions, respectively. Their morphological characters are in good agreements with the corresponding schematic modes of octahedral SnO₂, projected along the same direction (Figure 1e). The SAED pattern of an individual SnO₂ octahedron reveals it is a polycrystallite (inset in Figure 1 d, lower right). Figure S1 in the Supporting Information further reveals the hierarchical SnO₂ octahedron is composed of SnO₂ particles of approxi-

mately 30 nm. The HRTEM image shows the SnO₂ nanoparticles are single crystalline and the distances of lattice fringes were determined to be 0.333 and 0.267 nm, which can be indexed as (110) and (101) planes, respectively. The ideal model of SnO₂ octahedral shape (Figure 1 f) shows each face is a capped triangle-based pyramid, and the SnO₂ crystal is bound by eight {111} faces.^[14] In fact, each octahedron has eight triangles and the overall structure shares 12 identical edges.

To investigate the formation mechanism of octahedral $Sn_6O_4(OH)_4$ during the present sonochemical process, timedependent experiments were performed and the products

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were monitored by FE-SEM observations. Figure S2 in the Supporting Information displays a series of interesting images that show the morphological evolution of products synthesized at different sonication times (from 0 to 3 min). Without sonication (0 min), the products prepared after mixing SnCl₂·2H₂O and diethanolamine in a solvent mixture of DEG and water are nanoparticles (Figure S2a). After sonication for 1 min, the primary nanoparticles connected to each other assemble into nanorod and dendritic structures (Figure S2b). With the prolongation of the sonication reaction (3 min), the irregular $Sn_6O_4(OH)_4$ octahedra consisting of nanoparticles were observed and are shown in Figure S2c. Then, the $Sn_6O_4(OH)_4$ octahedra with smooth crystal faces can be achieved in terms of continuous surface flattening^[13] when the sonication reaction increased to 10 min, shown in Figure 1 b. Finally, after calcination in air at 800 °C for 3 h, hierarchical SnO₂ octahedra consisting of nanoparticles were obtained by the oxidization and decomposition of octahedral $Sn_6O_4(OH)_4$ intermediates.

According to the FE-SEM observations of the samples made at different sonication times, the possible growth process of octahedral SnO_2 through $Sn_6O_4(OH)_4$ intermediates is proposed and shown in Figure 2. Firstly, Sn₆O₄(OH)₄ nanorod and dendritic structures were formed through the self-assembly of nanoparticles, with the prolongation of ultrasonic reaction, rough octahedra consisting of nanoparticles were formed through the aggregation or assembly of nanoparticles, which form further $Sn_6O_4(OH)_4$ octahedra with smooth faces due to the surface flattening during the sonochemical process.^[13] Finally, after heat treatment at 800 °C for 3 h, the uniform hierarchical SnO₂ octahedra consisting of nanoparticles were obtained.

Sonication plays a crucial role in the present reproducible synthesis of uniform Sn₆O₄(OH)₄ octahedra with high yield because it is a rapid and efficient process. The sonochemical process generates localized hot spots with transient high temperatures of around 5000°C, pressures of about 1000 atm, and heating as well as cooling rates in excess of

Oriented Oriented eeeeee attachment attachment Sn₆O₄(OH)₄ Sn₆O₄(OH)₄ Oriented nanoparticles nanorod Dendritic Sn₆O₄(OH)₄ attachment Heat treatment Surface flattening Hierarchical SnO₂ Sn_O_(OH)_ Sn₆O₄(OH)₄ octahedron Octahedron consisting of octahedron consisting with smooth surfaces SnO₂ nanoparticles

1010 K s⁻¹, which will accelerate the synthesis of materials.^[15] DEG, a modified polyol,^[16] probably has dual roles, not only as a solvent but also as a coordination reagent to form Sn complexes, similar to the synthesis of ZnO spheres by a microwave process.^[17] Small primary Sn₆O₄(OH)₄ nuclei are generated by the hydrolysis of Sn complexes and then nanoparticles assemble through the same crystallographic orientation during the ultrasonic reaction. And the formation process of Sn₆O₄(OH)₄ octahedra can be ascribed to the well-known growth mechanism of oriented attachment^[18,19] and subsequent surface flattening.^[13]

Hierarchical SnO₂ octahedra were further used as photoelectrodes for DSSC applications. For DSSC fabrication, a compact TiO₂ blocking layer (≈ 300 nm thick consisting of 3-5 nm TiO₂ nanoparticles) was deposited between FTO glass and SnO₂ film by spin-coating (see the Experimental Section). Figure 3a shows the current-voltage (I-V) characteristics of the DSSCs based on various SnO₂ photoelectrodes. It is observed that the J_{sc} , V_{oc} and η are 10.96 mA cm⁻² 604 mV and 3.17%, respectively, for the SnO₂ octahedral



Figure 3. a) Photocurrent density-voltage curves of DSSCs based on hierarchical octahedral SnO₂ films with different thicknesses. □: 6.9, ○: 9.9, $\bigtriangleup:$ 13.2, $\bigtriangledown:$ 16.0, $\diamond:$ 18.8, \lhd and $\vartriangleright:$ 13.2 μm hierarchical octahedral SnO_2 film. \triangleleft is without TiCl₄ treatment and \triangleright is without both TiO₂ blocking layer and TiCl₄ treatment. b) Scheme of the SnO₂ film consisting of hierarchical SnO₂ octahedra (≈ 1 um in size) that are made of SnO₂ nanoparticles approximately 30 nm in diameter.

of nanoparticles

photoelectrode with TiO₂ blocking layer, which are much higher than that of 6.84 mA cm^{-2} , 543 mV, 2.07% for the electrode without TiO₂ blocking layer. The introduction of TiO₂ blocking layer was believed to effectively reduce the charge recombination at the FTO/electrolyte hence to improve the photocurrent density, photovoltage and power conversion efficiency.^[20] In addition, the higher density of the compact TiO₂ blocking layer, together with larger contact area and improved adherence between the SnO2 octahedra and FTO surface provides more electron pathways from SnO₂ film to FTO glass, which is helpful for electron transfer and subsequently enhances the electron transfer efficiency. The influence of TiCl₄ treatment on the photovoltaic parameters is further investigated. After the TiCl₄ treatment of the SnO₂ photoelectrodes, it is found that the photocurrent density and photovoltage increase from 10.96 mA cm^{-2} to 14.39 mA cm^{-2} , and 604 mV to 763 mV, respectively, resulting in a significant improvement of power conversion efficiency from 3.17% to 6.40%. The similar trend is also observed for the nanoparticles based DSSCs (Figure S3, Table S1). This can be ascribed to the significant reduction of the electron-hole recombination via the TiCl₄ treatment. The TiO₂ coating the SnO₂ surface will minimize defects at this internal surface, enabling ease of electron transfer from the TiO_2 to the SnO_2 and also avoid any extra internal trap sites which would otherwise be present in a poorly constructed junction.^[21] Moreover, recent researches for both liquid and solid state solar cells based on SnO₂ photoelectrode also supported our present results.^[10a,21]

Furthermore, the effects of SnO₂ film thickness on the photovoltaic performance are also investigated. The current-voltage (I-V) characteristics of the DSSCs based on hier-archical octahedral SnO₂ photoelectrodes with different thicknesses are shown in Figure 3a and the detailed photovoltaic parameters are summarized in Table 1. As shown in Figure 3a and Table 1, the short-circuit photocurrent density (J_{sc}) varied from 9.77 to 14.39 to 13.34 mA cm⁻², with a film thickness increase from 6.9 to 13.2 to 18.8 µm, accompanied with an increase in adsorbed dye amounts. The open-circuit

Table 1. Detailed photovoltaic parameters (J_{sc} , V_{oc} , FF, and η) of dye-sensitized SnO₂ solar cells with different film Thicknesses of hierarchical octahedral SnO₂ photoelectrodes.

Film thickness [µm]	$J_{\rm SC}$ [mA cm ⁻²]	V _{OC} [mV]	FF [%]	η [%]	Adsorbed dye $[\times 10^{-8} \mathrm{mol}\mathrm{cm}^{-2}]$
6.9	9.77	784	62.5	4.79	4.99
9.9	11.50	766	59.9	5.28	5.43
13.2	14.39	763	58.3	6.40	6.30
13.2 ^[a]	10.96	604	47.9	3.17	5.30
13.2 ^[b]	6.84	543	56.0	2.07	3.42
16.0	14.05	757	58.2	6.19	6.51
18.8	13.34	744	56.9	5.69	7.93
13.4 ^[c]	12.24	726	58.6	5.21	13.47

[a] Hierarchical octahedral SnO_2 film without TiCl₄ treatment. [b] Hierarchical octahedral SnO_2 film without both TiO₂ blocking and TiCl₄ treatment. [c] SnO_2 nanoparticle film synthesized by a sonochemical process in 50 mL aqueous solution containing $\text{SnCl}_2 \cdot 2 \text{ H}_2\text{O}$ (1.128 g) and diethanolamine (5.0 mL; without DEG).

voltage (V_{oc}) decreases with the increasing film thickness, due to the augmentation of the surface area providing additional charge-recombination sites and enhancing the dark current.^[7] Moreover, for thicker films the outer SnO₂ particle layers do not contribute significantly to the photogeneration of conduction band electrons due to the filtering of light by the dyed particles located close to the FTO glass.^[7] The sharing of photoinjected conduction band electrons by these particles lowers their quasi-Fermi level and hence the V_{oc} . The power conversion efficiency (η) of the solar cells increases from 4.79 to 6.40% and then decrease to 5.69% with the variations in film thickness.

For comparison, SnO₂ nanoparticles of around 40 nm (Figure S4 in the Supporting Information) have been prepared by a sonochemical process in a 50 mL aqueous solution containing SnCl₂·2H₂O (1.128 g) and diethanolamine (5.0 mL without DEG). The photovoltaic parameters of the DSSCs based on SnO₂ nanoparticles are $J_{sc} = 12.24 \text{ mA cm}^{-2}$, $V_{\rm oc}$ =726 mV, FF=58.6%, and energy conversion efficiency = 5.21% (Table 1). It is worth noting that highly efficiency (6.40%) DSSCs were obtained for the hierarchical SnO_2 octahedra, which is much higher than that of SnO₂ nanoparticles (5.21%). Such high photovoltaic performance is mainly ascribed to the novel bifunctional structure of hierarchical SnO₂ octahedra consisting of nanoparticles, in which SnO_2 nanoparticles (≈ 30 nm) can adsorb large amounts of dve and submicron octahedra ($\approx 1 \, \mu m$) can act as the light-scattering layer (shown in Figure 3b), which can significantly improve the photocurrent, voltage, and hence the photovoltaic performance. To the best of our knowledge, this is the first report on hierarchical octahedral SnO₂ material for solar cell applications and shows high power conversion efficiency.

The specific BET surface area of the hierarchical SnO₂ octahedra and nanoparticles are 26.3 and 33.9 m²g⁻¹, respectively, obtained from the N₂ adsorption-desorption measurements. Although both the surface area and adsorbed dye amounts of hierarchical SnO2 octahedra are smaller than the SnO₂ nanoparticles, the photovoltaic performance of DSSC based on the former is much higher than the latter. This can be attributed to the effective light scattering of hierarchical SnO₂ octahedra of 1.0 µm, and which is further characterized by the UV/Vis diffuse reflectance spectroscopy. The UV/Vis diffuse reflectance spectra of hierarchical SnO₂ octahedra and SnO₂ nanoparticle films with and without dye adsorption are shown in Figure 4. For the bare SnO₂ films (without dye adsorption), the reflectance of SnO₂ nanoparticles film is much lower than that of hierarchical SnO₂ octahedra film (Figure 4a), revealing the latter has a higher light-scattering ability than the former, caused by the submicron octahedra, which is in agreement with the previous results for the ZnO submicron spheres and nanoparticles.^[6] Furthermore, for the dye/SnO₂ film (Figure 4b), the dye-adsorbed hierarchical SnO₂ octahedra film shows a higher reflectance than the dye-adsorbed SnO₂ nanoparticles film in the long-wavelength region (550-700 nm) because of the light scattering from submicron octahedra. Hence, DSSCs

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Figure 4. Diffused reflectance spectra of the hierarchical SnO₂ octahedra (\Box) and SnO₂ nanoparticle films (\odot) with similar thickness ((13.3±0.1) µm). a) Without, and b) with adsorbed N719 dye.

based on the hierarchical SnO_2 octahedra exhibit superior photocurrent and photovoltaic performance than the SnO_2 nanoparticles, which is mainly attributed to the efficient light scattering for the former.

In summary, well-defined hierarchical SnO₂ octahedra consisting of nanoparticles have been successfully synthesized by a sonochemical process followed by heat treatment. The formation mechanism of octahedral Sn₆O₄(OH)₄ can be attributed to an oriented attachment based on time-dependent FE-SEM observations. The hierarchical octahedral SnO₂ shows high power conversion efficiency (6.40%) with a J_{sc} of 14.39 mA cm⁻² and a V_{oc} of 763 mV under simulated AM 1.5G one sun (100 mW cm⁻²) illumination for DSSC application. The power conversion efficiency (6.40%) of DSSC based on hierarchical SnO₂ octahedra has a 23% increase compared with that of SnO₂ nanoparticle photoelectrode (5.21%) is mainly ascribed to the efficient light scattering for the former, which is further confirmed by the UV/ Vis reflectance spectra.

Experimental Section

Synthesis: In a typical synthesis of $Sn_6O_4(OH)_4$ octahedra intermediates, $SnCl_2 \cdot 2H_2O$ was dissolved in the DEG, after 10 min stirring, deionized

water was added to this solution, and it was continuously stirred for 10 min. Afterwards, diethanolamine was added to this solution dropwise and it was stirred for a further 10 min, which resulted in the formation of a white suspension. Subsequently, the suspension was subjected to an intense ultrasonic irradiation (Sonics: VCX-500) for different time. The resulting precipitates were collected by centrifugation at 5000 rpm for 5 min and washed 5 times with absolute ethanol and distilled water, and finally dried at 60 °C for further characterization. To obtain hierarchical SnO₂ octahedra, part of the as-prepared samples were calcined at 800 °C for 3 h in air. For comparison, the synthesis of SnO₂ nanoparticles was also performed in the absence of DEG, while keeping other experimental conditions constant.

Fabrication of SnO₂ paste: Hierarchical SnO₂ octahedra (1.0 g) were ground for 40 min in a mixture of ethanol (8.0 mL), acetic acid (0.2 mL), terpineol (3.0 g), and ethyl cellulose (0.5 g) to form a slurry, and then the mixture was sonicated for 5 min in an ultrasonic bath to form a viscous white SnO₂ paste.

Preparation of the SnO₂ photoelectrode: The cleaned FTO glass (15 Ω / square, Nippon Sheet Glass, Japan) was first spin-coated with a compact TiO_2 blocking layer ≈ 300 nm thick. The anatase TiO_2 colloidal solution was prepared according to a modified literature procedure.^[22] Briefly, titanium n-butoxide (34.2 mL) was added slowly to a solution containing acetylacetone (10.2 mL) and n-butanol (37.6 mL) under stirring. Hydrolysis of the clear mixture was then performed by the dropwise addition of an aqueous acidic solution (para-toluenesulfonic acid (3.8 g) in H₂O (18.0 mL)). Stable transparent TiO2 (3-5 nm in particle size) was obtained after heating the mixture at 60 °C for 12 h. The hierarchical octahedral SnO2 paste was screen-printed onto the FTO glass containing the TiO₂ compact layer. The thickness of the SnO₂ film was easily controlled by repeated different screen-printing times. The SnO2 films were gradually heated under an air flow at 325 °C for 5 min, at 375 °C for 5 min, at 450°C for 15 min, and then at 500°C for 15 min. Then, the SnO₂ films were immersed into a 40 mM aqueous solution of TiCl4 at 70°C for 30 min and washed with water and ethanol, then sintered at 520 °C for 30 min. After cooling to 80 °C, the SnO₂ electrodes were put into 0.5 mm N719 dye ($[Ru{LL'-(NCS)_2}], L=2,2'$ -bipyridyl-4,4'-dicarboxylic acid, L= 2, 2'-bipyridyl-4, 4'-ditetrabutylammonium carboxylate, Solaronix) in ethanol, and was kept for 20 h at room temperature. The Pt-coated FTO counter electrode was prepared by dropping H_2PtCl_6 (5.0×10⁻⁴ M) solution on the FTO glass followed by heating at 400°C for 15 min in air. The electrolyte consisted of 1-propyl-3-methylimidazolium iodide (PMII, 0.6 M), I₂ (0.03 M), LiI (0.05 M), guanidine thiocyanate (GuNCS, 0.1 M, Aldrich), and 4-tert-butylpyridine (0.5 M, Aldrich) in acetonitrile and valeronitrile (85:15 v/v). The active area of the dye-coated SnO2 film was 0.16 cm², which was measured by profilometer (Ambios, XP-1).

Characterization: The phase purity of the products was characterized by powder XRD on a Bruker D8 Advance X-ray diffractometer using CuKa radiation ($\lambda = 1.5418$ Å). FE-SEM (JSM-6330F), transmission electron microscopy (TEM), high-resolution transmission electron microscopy (HRTEM), and selected-area electron diffraction (SAED) patterns were performed on a JEOL-2010 HR transmission electron microscope to characterize the morphology, size, and the intrinsic structure of the products. The N₂ adsorption-desorption isotherms of the hierarchical SnO₂ octahedra and nanoparticles were measured by using an ASAP 2010 surface-area analyzer (Micromeritics Instrument Corporation). UV/Vis diffuse reflectance spectra were measured on a UV/Vis-NIR spectrophotometer (UV, Shimadzu UV-3150). The adsorbed dye amounts were obtained by measuring the eluted dye concentration from the SnO₂ octahedra and nanoparticle films with the UV/Vis absorption spectroscopy. The thickness of the SnO2 film was measured by using a profilometer (Ambios, XP-1). The current-voltage characteristics were analyzed by using a Keithley 2400 source meter under simulated AM 1.5 G illumination (100 mW cm⁻²) provided by a solar simulator (69920, 1 kW Xe lamp, Oriel). The incident-light intensity was calibrated with a standard Si solar cell.

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